芯 伯 乐 ®
XINBOLE

Product Specification

XBLW 30N06
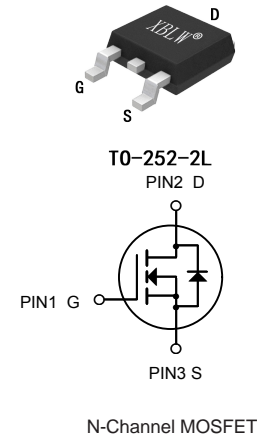
N-Channel Enhancement Mode MOSFET

RoHS

Description

The 30N06 uses advanced trench technology to provide excellent RDS(ON) , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

➢ TIVDS = 60V ID =30 A
➢ RDS(ON) < 26mΩ @ VGS= 10

Application

➢ Battery protection
➢ Load switch
➢ Uninterruptible power supply

TO−252−2L

PIN2 D

PIN1 G

PIN3 S

N-Channel MOSFET

Ordering Information

Product Model	Package Type	Marking	Packing	Packing Qty
XBLW 30N06	TO-252-2L	30N06	Tape	2500Pcs/Reel

Absolute Maximum Ratings (TC=25°Cunless otherwise noted)

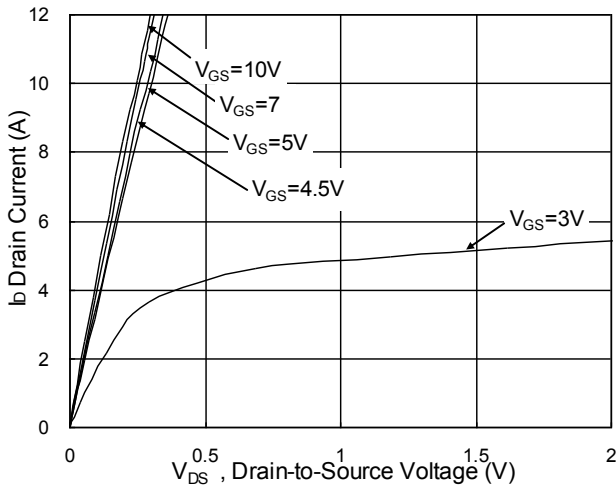| Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	60	V
VGS	Gate-Source Voltage	±20	V
ID@TC=25℃	Continuous Drain Current, VGS @ 10V1	30	A
ID@TC=100℃	Continuous Drain Current, VGS @ 10V1	15	A
ID@TA=25℃	Continuous Drain Current, VGS @ 10V1	5.6	A
ID@TA=70℃	Continuous Drain Current, VGS @ 10V1	4.5	A
IDM	Pulsed Drain Current2	46	A
EAS	Single Pulse Avalanche Energy3	25.5	mJ
IAS	Avalanche Current	22.6	A
PD@TC=25℃	Total Power Dissipation4	34.7	W
PD@TA=25℃	Total Power Dissipation4	2	W
TSTG	Storage Temperature Range	-55 to 150	℃
TJ	Operating Junction Temperature Range	-55 to 150	℃
RθJA	Thermal Resistance Junction-Ambient 1	62	℃/W
RθJC	Thermal Resistance Junction-Case1	3.6	℃/W

Electrical Characteristics (TJ=25 °C, unless otherwise noted)

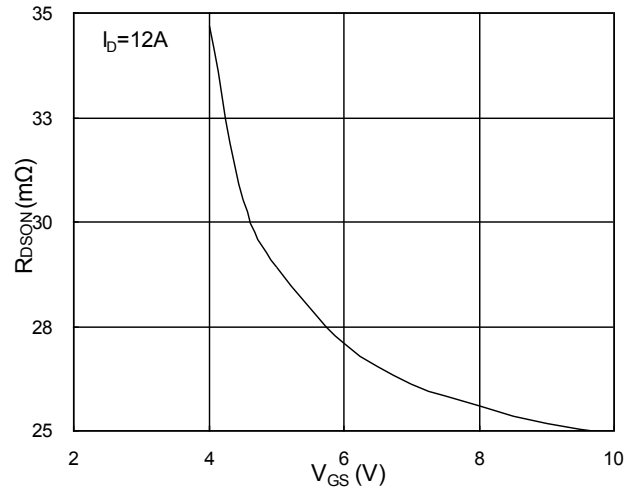| Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.063	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=15A	---	22	26	mΩ
		V_{GS}=4.5V , I_D=10A	---	30	38	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	---	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.24	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=$\pm$20V , V_{DS}=0V	---	---	$\pm$100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=15A	---	17	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	3.2	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=48V , V_{GS}=4.5V , I_D=12A	---	12.6	---	nC
Q_{gs}	Gate-Source Charge		---	3.2	---	
Q_{gd}	Gate-Drain Charge		---	6.3	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3.3 , I_D=10A	---	8	---	ns
T_r	Rise Time		---	14.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	24.4	---	
T_f	Fall Time		---	4.6	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	1378	---	pF
C_{oss}	Output Capacitance		---	86	---	
C_{rss}	Reverse Transfer Capacitance		---	64	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	23	A
I_{SM}	Pulsed Source Current[2,5]		---	---	46	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is VDD=25V,VGS=10V,L=0.1mH,IAS=22.6A

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.
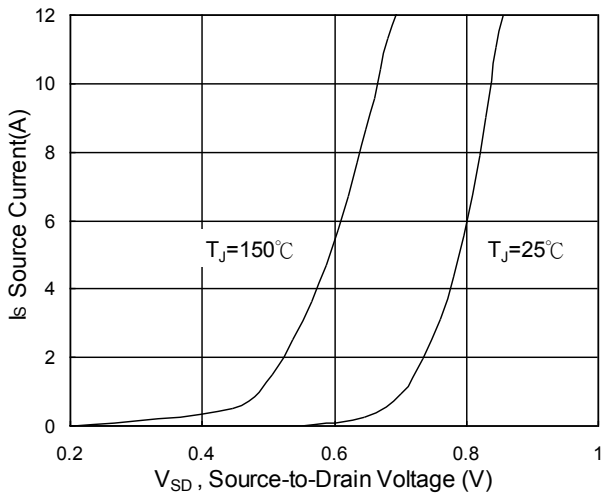
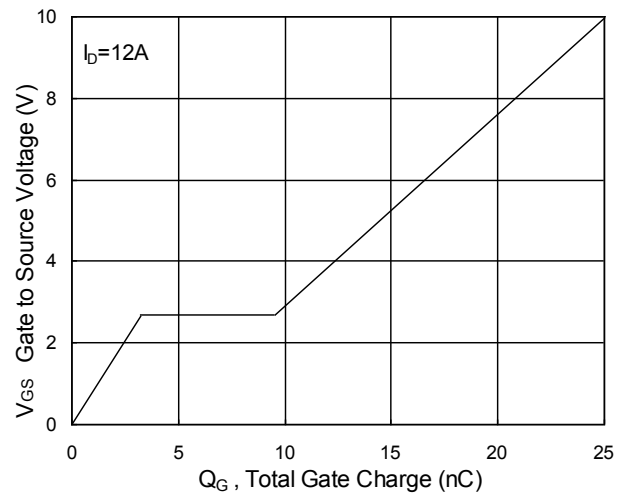## Typical Characteristics

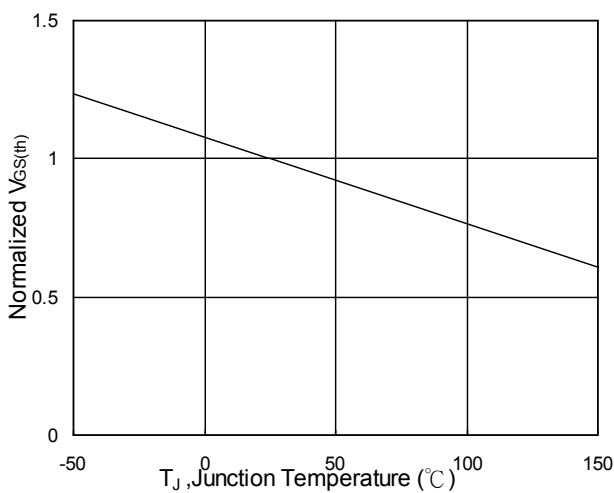**Fig.1 Typical Output Characteristics**

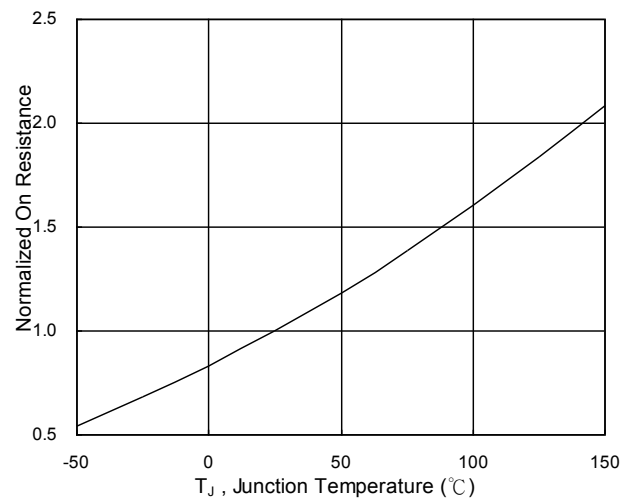**Fig.2 On-Resistance v.s Gate-Source**

Fig.3 Forward Characteristics of Reverse

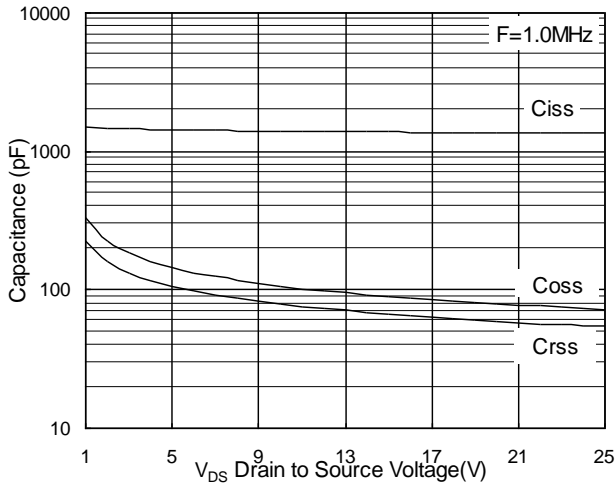**Fig.4 Gate-Charge Characteristics**

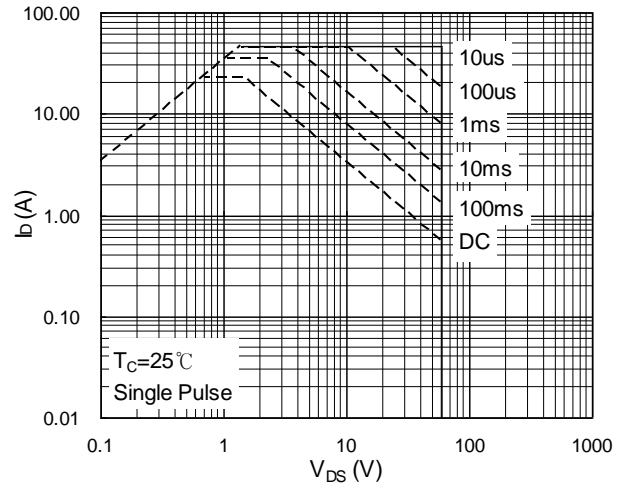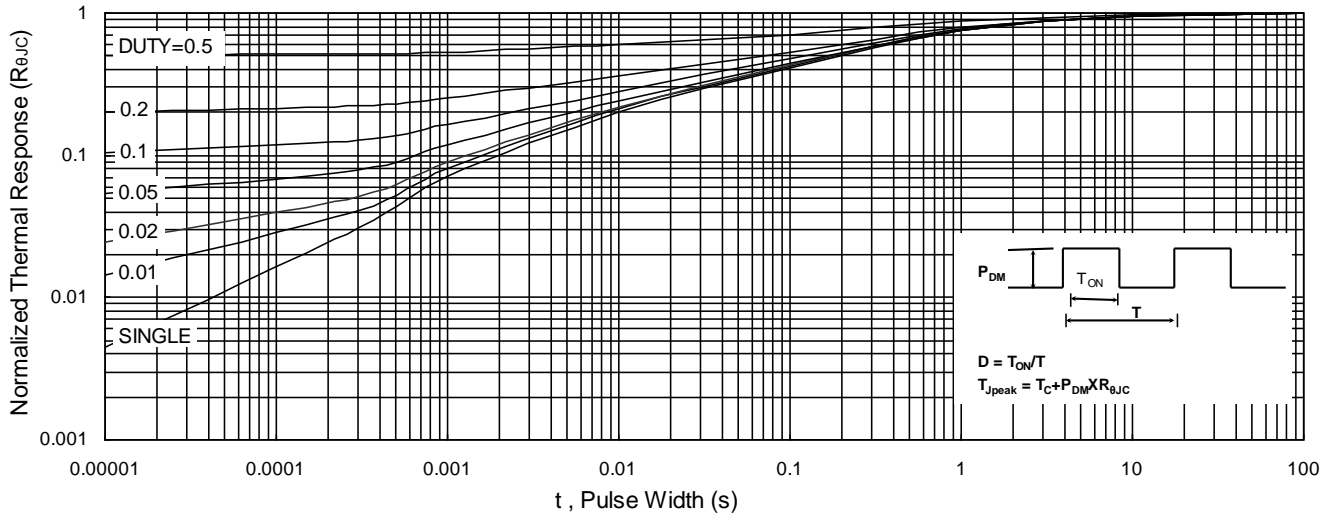**Fig.5 Normalized $V_{GS(th)}$ v.s T_J**

Fig.6 Normalized R_{DSON} v.s T_J

Fig.7 Capacitance

Fig.8 Safe Operating Area

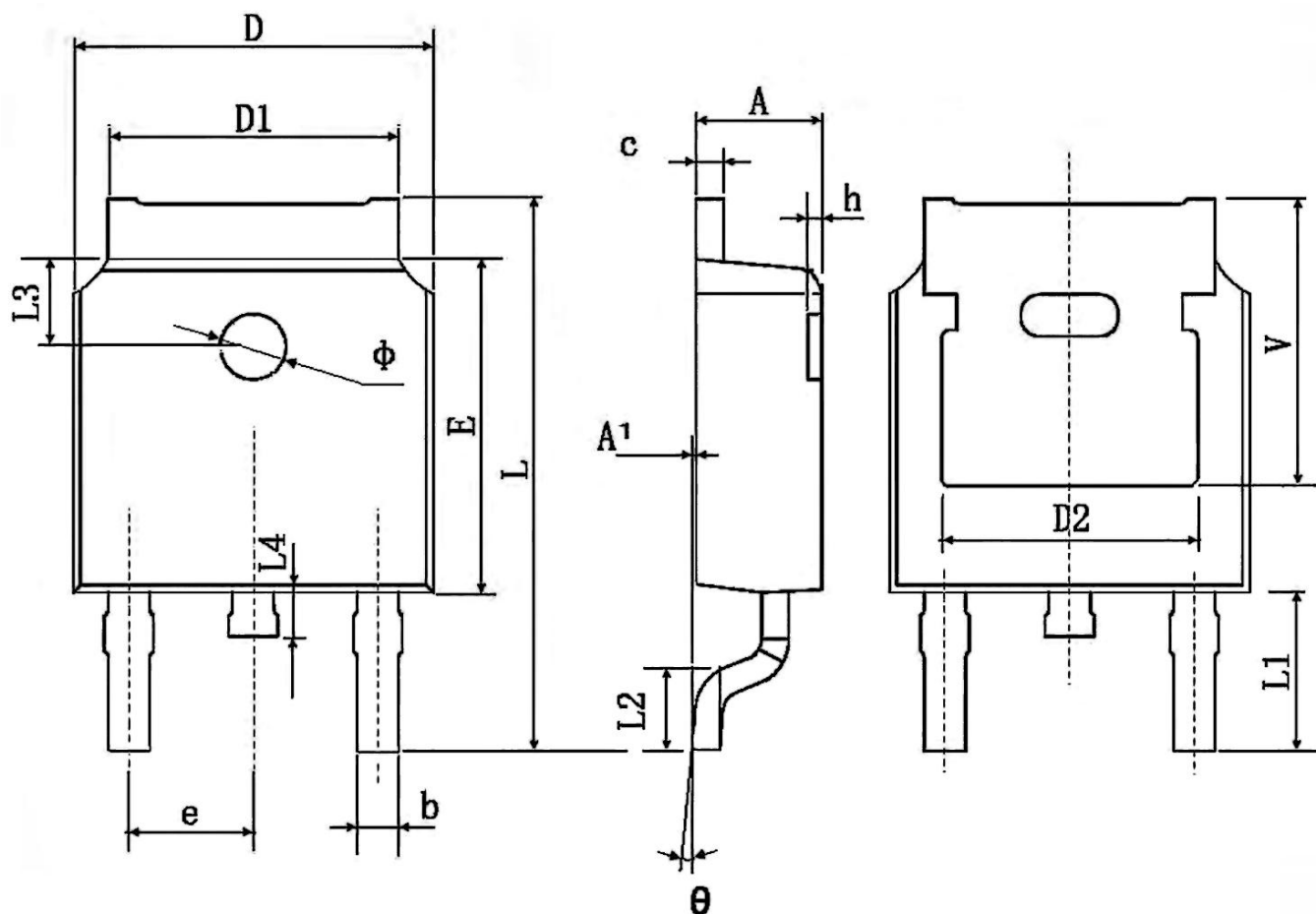**Fig.9 Normalized Maximum Transient Thermal Impedance**

$$EAS= \frac{1}{2}L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$

Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Waveform

Package Information

TO252-2L

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0。	8。	0。	8。
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

Statement：

- XBLW reserves the right to modify the product manual without prior notice! Before placing an order, customers need to confirm whether the obtained information is the latest version and verify the completeness of the relevant information.

- Any semi-guide product is subject to failure or malfunction under specified conditions. It is the buyer's responsibility to comply with safety standards when using XBLW products for system design and whole machine manufacturing. And take the appropriate safety measures to avoid the potential in the risk of loss of personal injury or loss of property situation!

- XBLW products have not been licensed for life support, military, and aerospace applications, and therefore XBLW is not responsible for any consequences arising from the use of this product in these areas.

- If any or all XBLW products (including technical data, services) described or contained in this document are subject to any applicable local export control laws and regulations, they may not be exported without an export license from the relevant authorities in accordance with such laws.

- The specifications of any and all XBLW products described or contained in this document specify the performance, characteristics, and functionality of said products in their standalone state, but do not guarantee the performance, characteristics, and functionality of said products installed in Customer's products or equipment. In order to verify symptoms and conditions that cannot be evaluated in a standalone device, the Customer should ultimately evaluate and test the device installed in the Customer's product device.

- XBLW documentation is only allowed to be copied without any alteration of the content and with the relevant authorization. XBLW assumes no responsibility or liability for altered documents.

- XBLW is committed to becoming the preferred semiconductor brand for customers, and XBLW will strive to provide customers with better performance and better quality products.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET *category:*

Click to view products by XBLW *manufacturer:*

Other Similar products are found below :

IRFD120 IRFY240C JANTX2N5237 2SK2267(Q) BUK455-60A/B MIC4420CM-TR VN1206L NDP4060 SI4482DY
IPS70R2K0CEAKMA1 SQD23N06-31L-GE3 TK16J60W,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG
DMN1053UCP4-7 SQJ469EP-T1-GE3 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR
DMN31D5UDJ-7 DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 STU5N65M6
DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 DMN2990UFB-7B IPB80P04P405ATMA2 2N7002W-G MCAC30N06Y-
TP MCQ7328-TP NTMC083NP10M5L NVMFS2D3P04M8LT1G BXP7N65D BXP4N65F AOL1454G WMJ80N60C4 BXP2N20L
BXP2N65D BXT1150N10J BXT1700P06M TSM60NB380CP ROG RQ7L055BGTCR DMNH15H110SK3-13